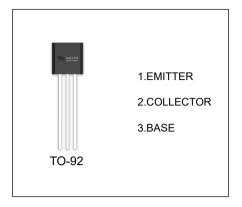


2SC1359 TRANSISTOR (NPN)

FEATURES

- Optimum for RF Amplification of FM/AM Radios.
- High Transition Frequency f_T.



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SC1359	TO-92	Bulk	1000pcs/Bag
2SC1359-TA	*^ -92	Таре	2000pcs/Box

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	30	V
V _{CEO}	Collector-Emitter Voltage	20	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current -Continuous	0.03	А
P _D	Collector Power Dissipation	400	mW
R _{0 JA}	Thermal Resistance from Junction o Ambient	312	°C /W
T_J , T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃



$T_a \text{=} 25\,^\circ\!\!\subset\,$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 0.1mA,I _E =0	30			٧
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA,I _B =0	20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =0.1mA,I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =10V,I _E =0			0.1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} =5V,I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =10V, I _C =1mA	70		220	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =15mA,I _B =1.5mA			0.2	V
Base-emitter saturation voltage	V _{BE (sat)}	I _C =15mA,I _B =1.5mA			1.2	V
Transition frequency	f _T	VcE=10V,Ic=1mA, f=200MHz	150			MHz

CLASSIFICATION OF h_{FE}

RANK	В	С
RANGE	70-140	110-220